

preliminary

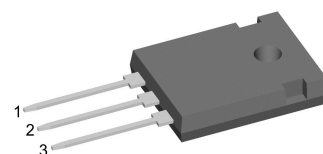
Schottky Diode Gen ²

$$\begin{aligned} V_{RRM} &= 60 \text{ V} \\ I_{FAV} &= 2 \times 30 \text{ A} \\ V_F &= 0.67 \text{ V} \end{aligned}$$

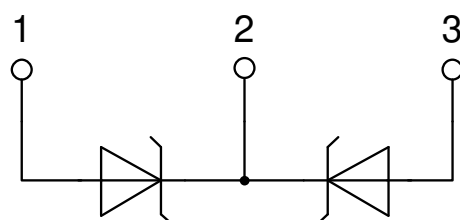
High Performance Schottky Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DSB60C60HB



Backside: cathode



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				60	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				60	V
I _R	reverse current, drain current	V _R = 60 V	T _{VJ} = 25°C			10	mA
		V _R = 60 V	T _{VJ} = 100°C			50	mA
V _F	forward voltage drop	I _F = 30 A	T _{VJ} = 25°C			0.77	V
		I _F = 60 A				1.18	V
		I _F = 30 A	T _{VJ} = 125°C			0.67	V
		I _F = 60 A				0.92	V
I _{FAV}	average forward current	T _C = 125°C rectangular d = 0.5	T _{VJ} = 150°C			30	A
V _{F0}	threshold voltage	} for power loss calculation only				0.46	V
r _F	slope resistance					6.2	mΩ
R _{thJC}	thermal resistance junction to case					0.95	K/W
R _{thCH}	thermal resistance case to heatsink				0.3		K/W
P _{tot}	total power dissipation	T _C = 25°C				130	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		570	A
C _J	junction capacitance	V _R = 12 V f = 1 MHz		T _{VJ} = 25°C		449	pF

preliminary

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			50	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Part description

D = Diode
 S = Schottky Diode
 B = ultra low VF
 60 = Current Rating [A]
 C = Common Cathode
 60 = Reverse Voltage [V]
 HB = TO-247AD (3)

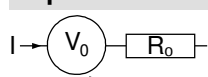
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSB60C60HB	DSB60C60HB	Tube	30	502935

Similar Part	Package	Voltage class
DSB60C60PB	TO-220AB (3)	60

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150^{\circ}\text{C}$

		Schottky	
$V_{0\max}$	threshold voltage	0.46	V
$R_{0\max}$	slope resistance *	3.7	mΩ

Outlines TO-247


Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215	BSC	5.46	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242	BSC	6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39

